

COFC

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Matthias Passlack et al.

) Patent No.: 6,756,320 B2

Application No.: 10/051,494

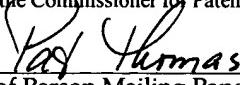
) Issue Date: June 29, 2004

Filed: January 18, 2002

) Docket No.: SC11692ZP

Title: ARTICLE COMPRISING AN OXIDE LAYER ON A GAAS-BASED
SEMICONDUCTOR STRUCTURECertificate of MailingDate of deposit: 4.3.06

I hereby certify that this paper is being deposited with the United States Postal Service on the date indicated above, as first-class mail, with sufficient postage attached thereto, in an envelope addressed to the Commissioner for Patents, Alexandria, VA 22313.


Signature of Person Mailing PaperPat Thomas
Printed Name of Person Mailing PaperCertificate of Corrections Branch
Commissioner for Patents
Alexandria, VA 22313Certificate
APR 11 2006
of CorrectionSUBMISSION OF CERTIFICATE OF CORRECTION

Dear Commissioner:

Enclosed, in duplicate, is a Certificate of Correction for errors in the subject patent.
Please enter these corrections.

Since the errors appear to be on the part of the United States Patent Office, there should be no charge.

Respectfully submitted,



Michael J. Balconi-Lamica
Attorney for Applicant(s)
Registration No. 43,629
Telephone No. (512) 996-6839
Facsimile No. (512) 996-6854

3/31/06
Date

APR 11 2006

Facsimile No. (512) 996-6854

PTO/SB/44 (04-05)

Approved for use through 04/30/2007 OMB 0651-0033

Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 1

PATENT NO.: 6,756,320 B2

APPLICATION NO: 10/051,494

DATE: June 29, 2004

INVENTOR(S): Matthias Passlack et al.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

In Column 6, Line 33, change "Ga²O³" to - -Ga₂O₃- -

In Column 6, Line 34, after "material" insert - -of Ga-Gd oxide- -

MAILING ADDRESS OF SENDER (Please do not use customer number below)

Freescale Semiconductor, Inc.

Law Department

7700 West Farmer Lane PL02

Austin, TX 78729

APR 11 2006

Facsimile No. (512) 996-6854

PTO/SB/44 (04-05)

Approved for use through 04/30/2007 OMB 0651-0033

Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 1

PATENT NO.: 6,756,320 B2

APPLICATION NO: 10/051,494

DATE: June 29, 2004

INVENTOR(S): Matthias Passlack et al.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

In Column 6, Line 33, change “Ga²O³” to - -Ga₂O₃- -

In Column 6, Line 34, after “material” insert - -of Ga-Gd oxide- -

MAILING ADDRESS OF SENDER (Please do not use customer number below)

Freescale Semiconductor, Inc.

Law Department

7700 West Parmer Lane PL02

Austin, TX 78729

APR 11 2006